

**isc Silicon NPN Power Transistor****2SC1008****DESCRIPTION**

- NPN high-voltage transistor
- Low current (max. 700 mA)

**APPLICATIONS**

- Designed for Switching and amplification in high voltage applications , such as telephony applications.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	80	V
$V_{CEO}$	Collector-Emitter Voltage	60	V
$V_{EBO}$	Emitter-Base Voltage	8	V
$I_C$	Collector Current-Continuous	0.7	A
$P_C$	Collector Power Dissipation @ $T_a < 50^{\circ}\text{C}$	0.8	W
J	Junction Temperature	-55~150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^{\circ}\text{C}$

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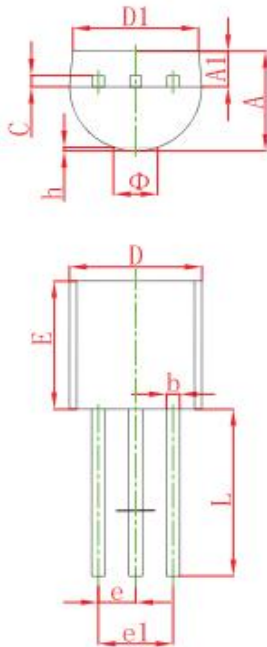
**2SC1008**

**ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 500mA; I <sub>B</sub> = 50mA			0.4	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 500mA; I <sub>B</sub> = 50mA			1.1	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 60V; I <sub>E</sub> = 0			0.1	uA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			0.1	uA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> =50mA ; V <sub>CE</sub> = 2V	40		400	

**TO-92 Package Outline Dimensions**



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.300	4.700	0.169	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270 TYP		0.050 TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Phi		1.600		0.063
h	0.000	0.380	0.000	0.015